
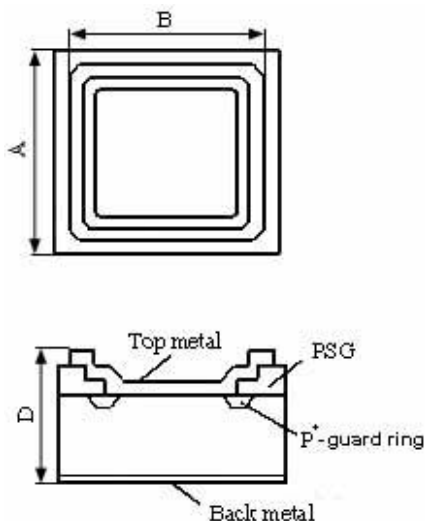


		5A/150V. Die Size-65mil.		
				
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10mA$	V_{BR}	V	150	160
Average Rectified Forward Current	$I_{F(AV)}$	A	5,0	-
DC Forward Voltage @ 25°C, $I_F=5,0A$	V_F	V	0,85	0,83
Maximum Reverse Current @ 25°C, $V_R=150V$ @ 25°C, $V_R=157V$ @ 125°C, $V_R=150V$	I_R	mA	0,005 - 5,0	0,003 0,010 4,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	110	-
Peak Repetitive Reverse Surge Current @ 2,0µs, f=1kHz., $T_J<175°C$.	I_{RRM}	A	2,0	-
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	V_{ESD}	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	°C	175	



DIM	ITEM	µm
A _x	Wafer Form Die Size	1650
A _y		1650
B _x	Top Metal Size	1510
B _y		1510
D	Thickness	300max.
Scribe line Width		80

Top metal:
a) **Al-Ni-Ag** – for Soldering;
b) **Al** – for Wire Bonding.
Backside metal: **Ti-Ni-Ag**.